### NOT RECOMMENDED FOR NEW DESIGN **USE DSS4160V**





# DNLS160V

### LOW V<sub>CE(SAT)</sub> NPN SURFACE MOUNT TRANSISTOR

### **Features**

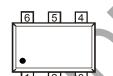
- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (DPLS160V)
- Surface Mount Package Suited for Automated Assembly
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 1)
- "Green Device" (Note 2)

**Mechanical Data** 

Case: SOT-563

Qualified to AEC-Q 101 Standards for High Reliability

SOT-563



Flammability Classification Rating 94V-0 Moisture Sensitivity: Level 1 per J-STD-020D

Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208

Case Material: Molded Plastic, "Green" Molding Compound. UL

- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.003 grams (approximate)

### Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Collector Current - Continuous	lc	1	Α
Peak Pulse Collector Current	I <sub>CM</sub>	2	Α
Base Current (DC)	I <sub>B</sub>	300	mA

### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C	$P_D$	300	mW
Thermal Resistance, Junction to Ambient (Note 3) @ T <sub>A</sub> = 25°C	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	$T_J$ , $T_{STG}$	-55 to +150	°C

Notes:

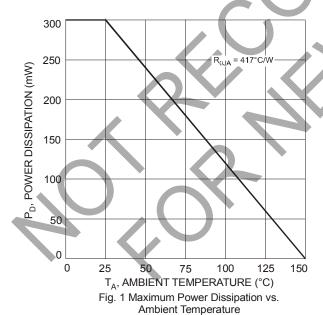
- No purposefully added lead.
- Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document P02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

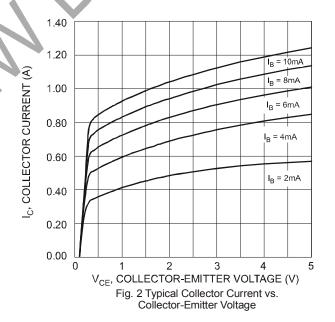


### **Electrical Characteristics** @TA = 25°C unless otherwise specified

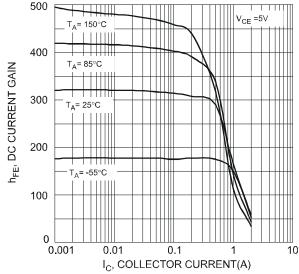
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	80	_		V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	60	_		V	$I_{C} = 10 \text{mA}, I_{B} = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	_	_	<b>V</b>	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	1			100	nA	$V_{CB} = 60V, I_{E} = 0$
Collector Cutoff Current	I <sub>CBO</sub>		_	50	μΑ	$V_{CB} = 60V, I_{E} = 0, T_{A} = 150^{\circ}C$
Collector Cutoff Current	I <sub>CES</sub>	_		100	nA	$V_{CE} = 60V, V_{BE} = 0$
Emitter Cutoff Current	I <sub>EBO</sub>	_		100	nA	$V_{EB} = 5V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)						
		250	320	_		$V_{CE} = 5V$ , $I_C = 1mA$
DC Current Gain	$h_{FE}$	200	280	_	V	$V_{CE} = 5V, I_{C} = 500mA$
		100	165	_	4	$V_{CE} = 5V$ , $I_C = 1A$
		_	80	110	_	$I_C = 100 \text{mA}, I_B = 1 \text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	_	80	140	mV	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
		_	140	250		$I_C = 1A$ , $I_B = 100mA$
Collector-Emitter Saturation Resistance	R <sub>CE(SAT)</sub>	_	140	250	mΩ	$I_C = 1A$ , $I_B = 100mA$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	0.91	1.1	V	$I_C = 1A$ , $I_B = 50mA$
Base-Emitter Turn On Voltage	V <sub>BE(ON)</sub>	_	0.81	0.9	V	$V_{CE} = 5V$ , $I_C = 1A$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C <sub>obo</sub>	_	7	10	pF	$V_{CB} = 10V, f = 1.0MHz$
Current Gain-Bandwidth Product	f <sub>T</sub>	150 🍙	270		MHz 🍓	$V_{CE} = 10V$ , $I_{C} = 50mA$ , $f = 100MHz$
SWITCHING CHARACTERISTICS			10 4			
Turn-On Time	t <sub>on</sub>		90		ns	
Delay Time	t <sub>d</sub>		17		ns	
Rise Time	t <sub>r</sub>	II - II	73	_//	ns	V <sub>CC</sub> = 10V
Turn-Off Time	toff		300		ns	$I_C = 0.5A$ , $I_{B1} = I_{B2} = 25mA$
Storage Time	ts	1	220		ns	
Fall Time	t <sub>f</sub>	- T	80	7	ns	
	W - W	400	-	- 100	~	

Notes: 4. Measured under pulsed conditions. Pulse width =  $300\mu s$ . Duty cycle  $\leq 2\%$ .

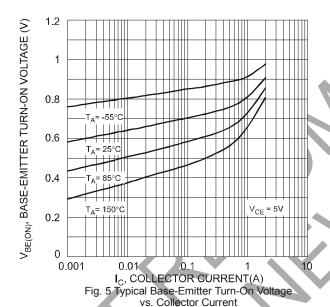


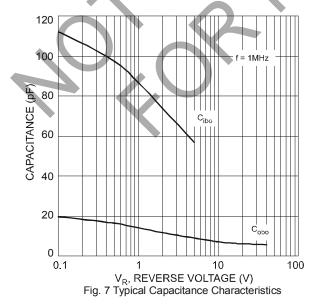












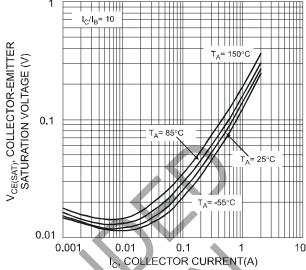


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

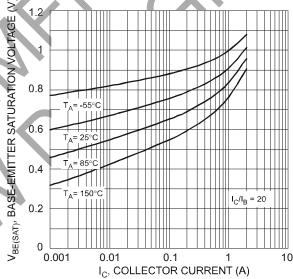
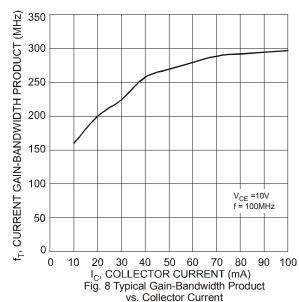


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current



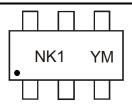


### **Ordering Information** (Note 5)

Device	Packaging	Shipping
DNLS160V-7	SOT-563	3000/Tape & Reel

5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

### **Marking Information**

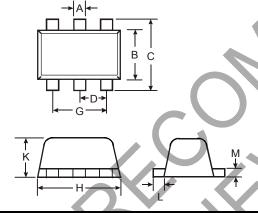


NK1 = Product Type Marking Code YM = Date Code Marking Y = Year ex: V = 2008 M = Month ex: 9 = September

### Date Code Key

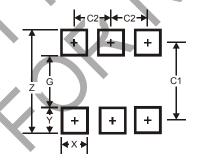
Year	2008		2009	2010	١	2011	2012		2013	2014		2015
Code	V		W	Х		Υ	Z		Α	В		С
			1	1	1	1	-					1
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

## **Package Outline Dimensions**



_	~	_			
SOT-563					
Dim	Min	Max	Тур		
A	0.15	0.30	0.20		
В	1.10	1.25	1.20		
O	1.55	1.70	1.60		
D	-	-	0.50		
G	0.90	1.10	1.00		
Н	1.50	1.70	1.60		
K	0.55	0.60	0.60		
L	0.10	0.30	0.20		
M	0.10	0.18	0.11		
All Dimensions in mm					

### Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Y	0.5
C1	1.7
C2	0.5

### IMPORTANT NOTICE

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Diodes Incorporated does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on our website, harmless against all damages.

### LIFE SUPPORT

Diodes Incorporated products are not authorized for use as critical components in life support devices or systems without the expressed written approval of the President of Diodes Incorporated.